

Gordon Schmidt

List of Publications by Year in descending order

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papers

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times ranked

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#	ARTICLE	IF	CITATIONS
1	Desorption induced formation of low-density GaN quantum dots: nanoscale correlation of structural and optical properties. <i>Journal Physics D: Applied Physics</i> , 2022, 55, 145102.	1.3	0
2	Direct Imaging of the Carrier Capture into Individual InP Quantum Dots of a Semiconductor Disk Laser Membrane. <i>ACS Nano</i> , 2022, 16, 4619-4628.	7.3	0
3	Color-Tunable 3D InGaN/GaN Multi-Quantum-Well Light-Emitting Diode Based on Microfacet Emission and Programmable Driving Power Supply. <i>Advanced Optical Materials</i> , 2021, 9, .	3.6	14
4	Demonstration of lateral epitaxial growth of AlN on Si (1 1 1) at low temperatures by pulsed reactive sputter epitaxy. <i>Journal of Crystal Growth</i> , 2021, 571, 126250.	0.7	6
5	Cathodoluminescence nano-characterization of individual GaN/AlN quantum disks embedded in nanowires. <i>Applied Physics Letters</i> , 2020, 117, 133106.	1.5	3
6	Optical and Structural Properties of Nitride Based Nanostructures. <i>Springer Series in Solid-state Sciences</i> , 2020, , 135-201.	0.3	2
7	Individually resolved luminescence from closely stacked GaN/AlN quantum wells. <i>Photonics Research</i> , 2020, 8, 610.	3.4	8
8	Ordered arrays of defect-free GaN nanocolumns with very narrow excitonic emission line width. <i>Journal of Crystal Growth</i> , 2019, 525, 125189.	0.7	7
9	Intensive luminescence from a thick, indium-rich In _{0.7} Ga _{0.3} N film. <i>Japanese Journal of Applied Physics</i> , 2019, 58, 065503.	0.8	2
10	Outstanding Reliability of Heavy-Ion-Irradiated AlInN/GaN on Silicon HFETs. <i>IEEE Transactions on Nuclear Science</i> , 2019, 66, 2417-2421.	1.2	4
11	Direct imaging of Indium-rich triangular nanoprisms self-organized formed at the edges of InGaN/GaN core-shell nanorods. <i>Scientific Reports</i> , 2018, 8, 16026.	1.6	19
12	Compositionally graded InGaN layers grown on vicinal N-face GaN substrates by plasma-assisted molecular beam epitaxy. <i>Journal of Crystal Growth</i> , 2017, 465, 55-59.	0.7	16
13	Nanoscale Imaging of Structural and Optical Properties Using Helium Temperature Scanning Transmission Electron Microscopy Cathodoluminescence of Nitride Based Nanostructures. <i>Microscopy and Microanalysis</i> , 2016, 22, 600-601.	0.2	3
14	Nanoscale Cathodoluminescence of an InGaN Single Quantum Well Intersected by Individual Dislocations. <i>Microscopy and Microanalysis</i> , 2016, 22, 602-603.	0.2	0
15	Embedded GaN nanostripes on sapphire for DFB lasers with semipolar quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 180-185.	0.7	5
16	Defect reduced selectively grown GaN pyramids as template for green InGaN quantum wells. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 67-72.	0.7	2
17	Nanoscale cathodoluminescence of stacking faults and partial dislocations in a-plane GaN. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 73-77.	0.7	2
18	Nanoscale cathodoluminescence imaging of III-nitride-based LEDs with semipolar quantum wells in a scanning transmission electron microscope. <i>Physica Status Solidi (B): Basic Research</i> , 2016, 253, 112-117.	0.7	7

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19	Structural and optical nanoscale analysis of GaN core-shell microrod arrays fabricated by combined top-down and bottom-up process on Si(111). Japanese Journal of Applied Physics, 2016, 55, 05FF02.	0.8	4
20	Clustered quantum dots in single GaN islands formed at threading dislocations. Japanese Journal of Applied Physics, 2016, 55, 05FF04.	0.8	5
21	Metalorganic chemical vapor phase epitaxy of narrow-band distributed Bragg reflectors realized by GaN:Ge modulation doping. Journal of Crystal Growth, 2016, 440, 6-12.	0.7	11
22	Direct evidence of single quantum dot emission from GaN islands formed at threading dislocations using nanoscale cathodoluminescence: A source of single photons in the ultraviolet. Applied Physics Letters, 2015, 106, .	1.5	29
23	Growth of AlInN/GaN distributed Bragg reflectors with improved interface quality. Journal of Crystal Growth, 2015, 414, 105-109.	0.7	22
24	Optical Emission of Individual GaN Nanocolumns Analyzed with High Spatial Resolution. Nano Letters, 2015, 15, 5105-5109.	4.5	35
25	Advances in MBE Selective Area Growth of III-Nitride Nanostructures: From NanoLEDs to Pseudo Substrates. International Journal of High Speed Electronics and Systems, 2014, 23, 1450020.	0.3	4
26	Extended defects in GaN nanocolumns characterized by cathodoluminescence directly performed in a transmission electron microscope. Turkish Journal of Physics, 2014, 38, 323-327.	0.5	0
27	Growth of InGaN/GaN core-shell structures on selectively etched GaN rods by molecular beam epitaxy. Journal of Crystal Growth, 2014, 392, 5-10.	0.7	13
28	Nano-scale luminescence characterization of individual InGaN/GaN quantum wells stacked in a microcavity using scanning transmission electron microscope cathodoluminescence. Applied Physics Letters, 2014, 105, 032101.	1.5	30
29	Direct nano-scale correlation of structural and optical properties of lattice matched AlInN/AlGaN DBRs using helium temperature scanning transmission electron microscopy cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1874-1875.	0.2	1
30	Direct imaging of GaN Pyramids covered by InGaN Single Quantum Well using nano-scale Scanning Transmission Electron Microscopy Cathodoluminescence. Microscopy and Microanalysis, 2012, 18, 1838-1839.	0.2	1
31	Cathodoluminescence directly performed in a transmission electron microscope: nanoscale correlation of structural and optical properties. Microscopy and Microanalysis, 2012, 18, 1834-1835.	0.2	1
32	Growth and stacking fault reduction in semi-polar GaN films on planar Si(112) and Si(113). Physica Status Solidi C: Current Topics in Solid State Physics, 2012, 9, 507-510.	0.8	16